Amendments to the Claims

Claims 1-54 are cancelled.

55. (Currently amended) A method of forming a capacitor comprising:

providing a substrate having a node location disposed between a ~~pair of~~ first conductive line and a second conductive line ~~lines~~;

forming a contact structure in electrical communication with the node location, the contact structure extending laterally over at least a portion of each of the conductive lines; and

forming ~~a pair of~~ capacitor containers in electrical communication with the node location, the ~~pair of~~ capacitor containers consisting of ~~having~~ a first container disposed at least partially over only the first ~~a~~ first conductive line ~~comprised by the pair of conductive lines and a~~ and a second container disposed at least partially over ~~a~~ only the second conductive line ~~comprised by the pair of conductive lines~~, the first container being spaced from the second ~~capacitor~~ container.

56. (Currently amended) The method of claim 55 wherein the forming the ~~pair of~~ capacitors comprises:

forming a masking layer over the substrate and over the conductive lines;

forming a first opening within the masking layer over the first conductive line;

forming a second opening ~~over~~ within the masking layer over the second conductive line; and

depositing a conductive material within the first and second openings, the conductive material being in direct physical contact with the contact structure.

57. (Previously presented) The method of claim 56 wherein the conductive material comprises polysilicon.

58. (Currently amended) The method of claim 55 further comprising:

lining the ~~pair of~~ capacitor containers with a dielectric material; and

forming a capacitor electrode layer over the dielectric material and within the first and second containers.

59. (Currently amended) A method of forming a capacitor structure comprising:

providing a substrate having a substrate node location;

forming a contact structure in electrical communication with the substrate node location, the contact structure being disposed between two conductive lines, ~~and~~ extending elevationally above and laterally outward over and contacting an uppermost surface of each of the two conductive lines;

forming a first container having a continuous conductive layer defining a first interior area, the conductive layer being joined with the contact structure, the first container being disposed at least partially over one of the two conductive lines;

forming a second container having a continuous conductive layer defining a second interior area, the conductive layer being joined with the contact structure, the first

and second interior areas being spaced apart from one another in a non-overlapping relationship; and

forming a dielectric layer and a conductive capacitor electrode layer disposed operably proximate the first container the second container and portions of the contact structure.

60. (Previously presented) The method of claim 59, wherein the containers are elongate and extend along generally parallel central axes.

61. (Currently amended) The method of claim 59, wherein the capacitor ~~comprises only two~~ containers are laterally separated by a dielectric region, at least one of the containers being elongate and generally tubular in shape.

62. (Currently amended) A method of forming DRAM circuitry comprising:

providing a substrate having first and second spaced apart node locations;

forming a first storage capacitor in electrical communication with the first node location and comprising capacitor containers consisting of first and second containers, the first container being at least partially disposed over a first conductive line, the second container being disposed at least partially over a second conductive line;

forming a second storage capacitor in electrical communication with the second node location and comprising capacitor containers consisting of third and fourth containers, the third container being disposed at least partially over a third conductive line, the fourth container being at least partially disposed over a fourth conductive line;

lining the first, second third and fourth containers with a dielectric layer; and

depositing a conductive capacitor electrode layer over the dielectric layer and within the containers.

63. (Previously presented) The method of claim 62, wherein the containers are generally elongate.

64. (Previously presented) The method of claim 62, wherein the containers are generally elongate and extend along respective central axes at least two of which being generally parallel.

65. (Previously presented) The method of claim 62, wherein the containers are generally elongate and extend along respective central axes which are generally parallel with one another.

66. (Previously presented) The method of claim 62, wherein the containers are generally elongate and extend along respective central axes, and wherein each container comprises a respective portion which has a generally circular transverse cross-section.

67. (Previously presented) The method of claim 62, wherein each container has a volume which is substantially equivalent relative to the each other.